

Vishay Semiconductors

TELUX™ LED



DESCRIPTION

The TELUX™ series is a clear, non diffused LED for high end applications where supreme luminous flux is required.

It is designed in an industry standard 7.62 mm square package utilizing highly developed (AS) AllnGaP and InGaN technologies.

The supreme heat dissipation of TELUX[™] allows applications at high ambient temperatures.

All packing units are binned for luminous flux and color to achieve best homogenous light appearance in application.

FEATURES





· High luminous flux

- Supreme heat dissipation: R_{th.IP} is 90 K/W
- High operating temperature: T_i up to + 125 °C
- Type TLWR meets SAE and ECE color requirements
- · Packed in tubes for automatic insertion
- · Luminous flux and color categorized for each tube
- Small mechanical tolerances allow precise usage of external reflectors or lightguides
- TLWR and TLWY types additionally forward voltage categorized
- ESD-withstand voltage: > 2 kV acc. to MIL STD 883
 D, Method 3015.7 for AllnGaP, > 1 kV for InGaN
- · Lead (Pb)-free device

APPLICATIONS

- Exterior lighting
- · Dashboard illumination
- Tail-, stop and turn signals of motor vehicles
- Replaces incandescent lamps
- Traffic signals and signs

PRODUCT GROUP AND PACKAGE DATA

Product group: LED
 Package: TELUX™
 Product series: standard

Angle of half intensity: ± 30°

PARTS TABLE		
PART	COLOR, LUMINOUS INTENSITY	TECHNOLOGY
TLWR7601	Red, $\phi_V = (1500 \text{ to } 3600) \text{ mlm}$	AllnGaP on GaAs

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ABSOLUTE MAXIMUM RATINGS ¹⁾ TLWR7601							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
Reverse voltage	I _R = 10 μA	V _R	10	V			
DC Forward current	T _{amb} ≤ 85 °C	I _F	70	mA			
Surge forward current	t _p ≤ 10 μs	I _{FSM}	1	Α			
Power dissipation	T _{amb} ≤ 85 °C	P _V	187	mW			
Junction temperature		T _j	125	°C			
Operating temperature range		T _{amb}	- 40 to + 110	°C			
Storage temperature range		T _{stg}	- 55 to + 110	°C			
Soldering temperature	$t \le 5$ s, 1.5 mm from body preheat temperature 100 °C/30 s	T_{sd}	260	°C			
Thermal resistance junction/ ambient	with cathode heatsink of 70 mm ²	R _{thJA}	200	K/W			
Thermal resistance junction/pin	with cathode heatsink of 70 mm ²	R _{thJP}	90	K/W			

 $^{^{1)}}$ T_{amb} = 25 °C, unless otherwise specified

OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ TLWR7601, RED								
PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP.	MAX	UNIT		
Total flux	$I_F = 70 \text{ mA}, R_{thJA} = 200 \text{ °K/W}$	φV	1500	2100	3600	mlm		
Luminous intensity/Total flux	$I_F = 70 \text{ mA}, R_{thJA} = 200 \text{ °K/W}$	I_V/ϕ_V		0.8		mcd/mlm		
Dominant wavelength	$I_F = 70$ mA, $R_{thJA} = 200$ °K/W	λ_{d}	611	618	634	nm		
Peak wavelength	$I_F = 70$ mA, $R_{thJA} = 200$ °K/W	λ_{p}		624		nm		
Angle of half intensity	$I_F = 70$ mA, $R_{thJA} = 200$ °K/W	φ		± 30		deg		
Total included angle	90 % of total flux captured	φ		75		deg		
Forward voltage	$I_F = 70 \text{ mA}, R_{thJA} = 200 \text{ °K/W}$	V _F	1.83	2.2	2.67	V		
Reverse voltage	I _R = 10 μA	V _R	10	20		V		
Junction capacitance	V _R = 0, f = 1 MHz	C _j		17		pF		
Temperature coefficient of λ_{dom}	I _F = 50 mA	TCλ _{dom}		0.05		nm/K		

Note:

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

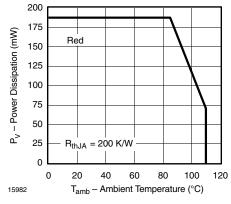


Figure 1. Power Dissipation vs. Ambient Temperature

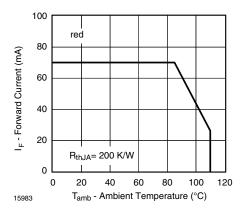


Figure 2. Forward Current vs. Ambient Temperature

 $^{^{1)}}$ T_{amb} = 25 °C, unless otherwise specified





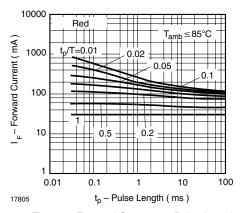


Figure 3. Forward Current vs. Pulse Length

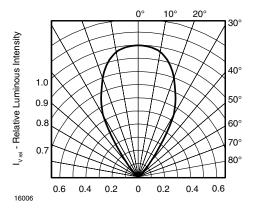


Figure 4. Rel. Luminous Intensity vs. Angular Displacement for 60° emission angle

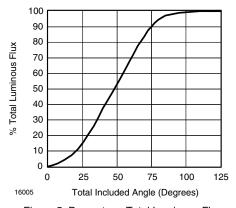


Figure 5. Percentage Total Luminous Flux vs. Total Included Angle for 60 $^{\circ}$ emission angle

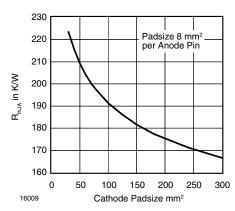


Figure 6. Thermal Resistance Junction Ambient vs.

Cathode Padsize

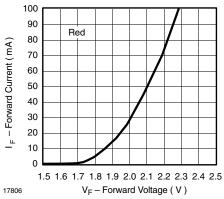


Figure 7. Forward Current vs. Forward Voltage

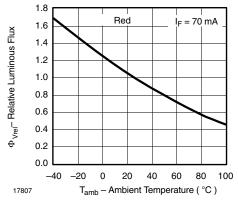


Figure 8. Rel. Luminous Flux vs. Ambient Temperature

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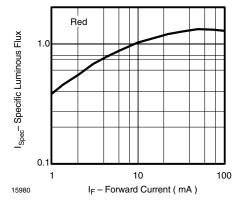


Figure 9. Specific Luminous Flux vs. Forward Current

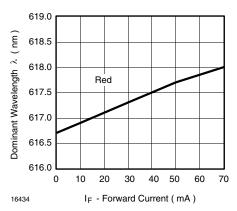


Figure 12. Dominant Wavelength vs. Forward Current

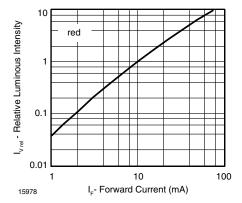


Figure 10. Relative Luminous Flux vs. Forward Current

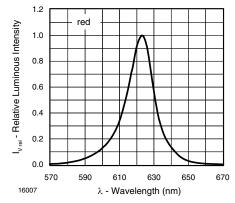
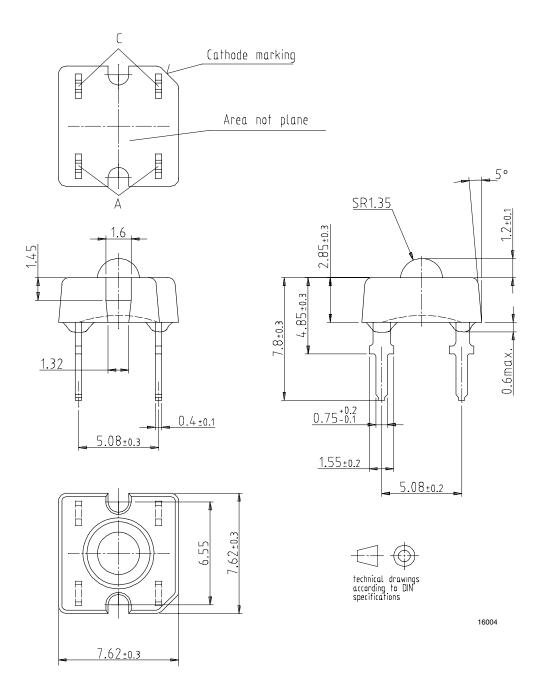


Figure 11. Relative Intensity vs. Wavelength





PACKAGE DIMENSIONS in millimeters



TLWR7601

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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

> We reserve the right to make changes to improve technical design and may do so without further notice.

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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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